

In the Specification:

Please replace paragraph 0002 with the following corrected paragraph:

[0002] When MOSFET gate length is scaled below 100 nanometers (nm), short channel effects become significant factors. Strong or higher implant dose super halo implants are widely used in deep submicron CMOS technology to engineer the FET channel to overcome short channel effects. Super halo implants, however, tend to degrade the source/drain junction capacitance, resulting in slower switching speed of the transistor. What is needed is a method to engineer the channel doping profile without affecting the source/drain junction region to overcome the short channel effects in deep submicron CMOS chips having gate lengths of 50 nm or less.

In the Claims:

Please cancel claim 7 without prejudice.